



Atty. Docket No. 8013-4655

PATENTS

enterin
part

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Atsushi YAMAGUCHI et al.

Confirmation No. 6543

Serial No. 09/816,754

GROUP 2826

Filed March 26, 2001

Examiner Remmon R. Forde

NITRIDE BASED SEMICONDUCTOR PHOTO-
LUMINESCENT DEVICE

AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

Responsive to the Official Action of July 3, 2002,
please amend the above-identified application as follows:

IN THE ABSTRACT:

Rewrite the Abstract of the Disclosure as on the
accompanying separate sheet.

IN THE SPECIFICATION:

Page 8, replace the paragraph, beginning on line 11, as
follows:

--The technique for doping silicon into the active
layer has been used for improving the laser device performances
such as the threshold current density. In Japanese laid-open
patent publication No. 10-12969, it is disclosed that silicon
impurity is doped into the active layer at an impurity

TECHNOLOGY CENTER 2801

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